

## General Description

The MY30N15D uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

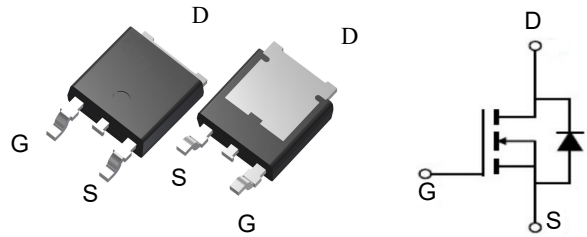


## Features

$V_{DSS}$	150	V
$I_D$	30	A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	<46	$m\Omega$
$R_{DS(ON)}$ (at $V_{GS}=4.5V$ )	<50	$m\Omega$

## Application

- Battery protection
- Load switch
- Uninterruptible power supply



## Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY30N15D	TO-252-2L	MY30N15D	2500

## Absolute Maximum Ratings ( $T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	150	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	30	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	22	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	60	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	216	mJ
$I_{AS}$	Avalanche Current	38	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>3</sup>	115	W
$T_{STG}$	Storage Temperature Range	-55 to 175	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 175	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	55	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	1.3	$^\circ C/W$

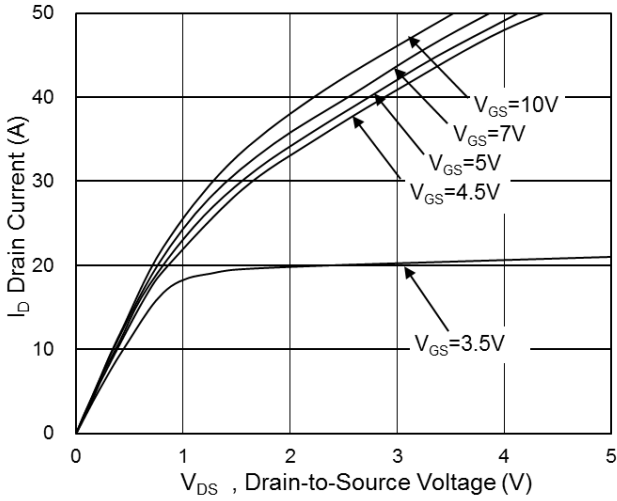
**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	150	---	---	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =20A	---	35	46	mΩ
	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V , I <sub>D</sub> =20A	---	37	50	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	---	2.5	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =120V , V <sub>GS</sub> =0V , T <sub>J</sub> =25 °C	---	---	1	uA
		V <sub>DS</sub> =120V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =20A	---	55	---	S
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =75V , V <sub>GS</sub> =4.5V , I <sub>D</sub> =10A	---	40	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	10	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	21	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =50V , V <sub>GS</sub> =4.5V , R <sub>G</sub> =3.3 I <sub>D</sub> =10A	---	18	---	ns
T <sub>r</sub>	Rise Time		---	20	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	65	---	
T <sub>f</sub>	Fall Time		---	15	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V , V <sub>GS</sub> =0V , f=1MHz	---	3755	---	pF
C <sub>oss</sub>	Output Capacitance		---	207	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	160	---	
I <sub>s</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	---	---	30	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>s</sub> =1A , T <sub>J</sub> =25°C	---	---	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =10A , dI/dt=100A/μs , T <sub>J</sub> =25°C	---	35	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	120	---	nC

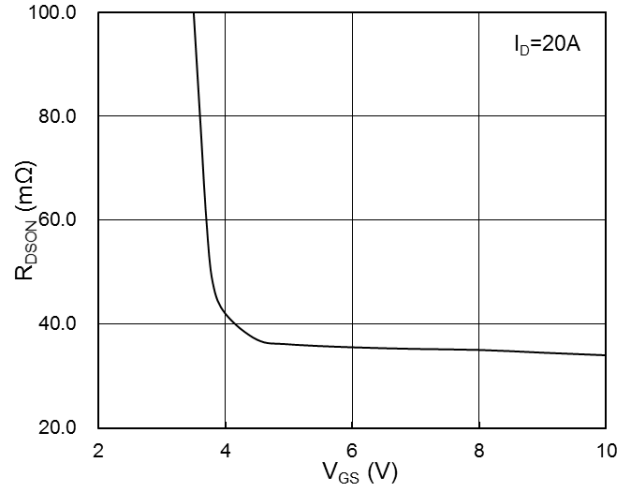
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3 .The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V,V<sub>GS</sub>=10V,L=0.3mH,I<sub>AS</sub>=38A
- 4.The power dissipation is limited by 150°C junction temperature
- 5 .The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.

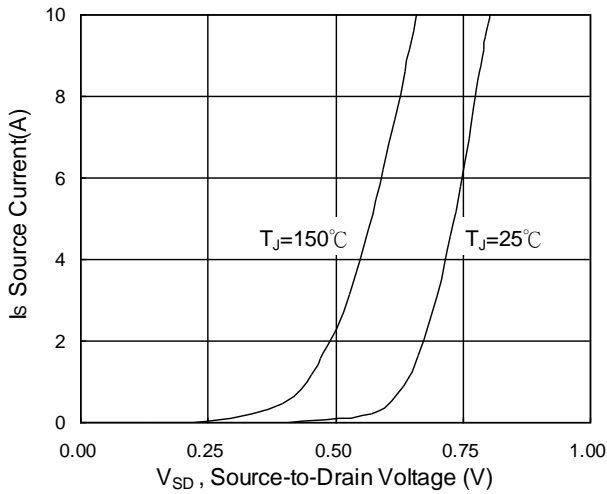
**Typical Characteristics**



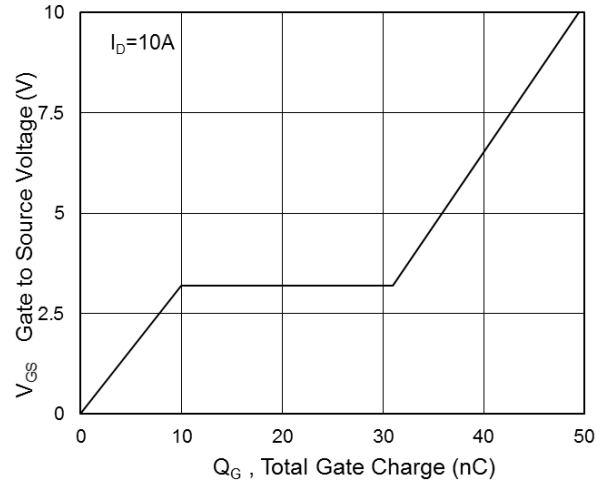
**Fig.1 Typical Output Characteristics**



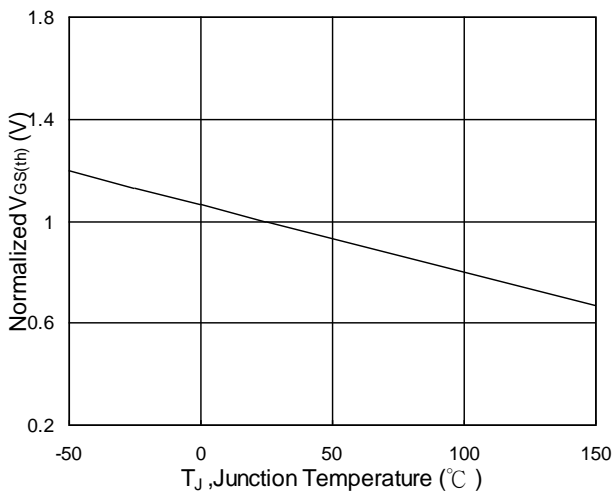
**Fig.2 On-Resistance vs. Gate-Source**



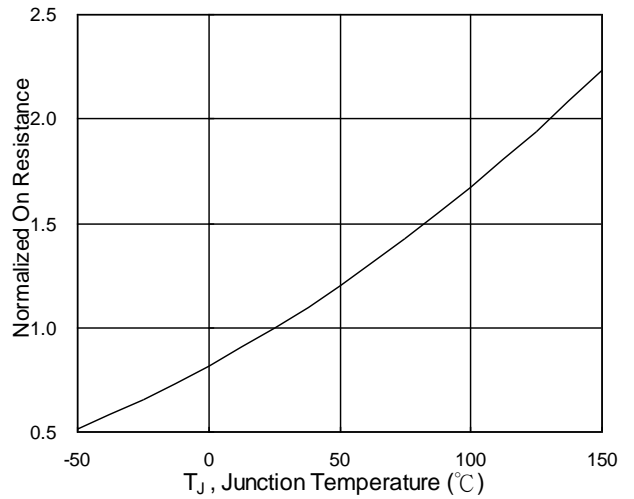
**Fig.3 Forward Characteristics Of Reverse**



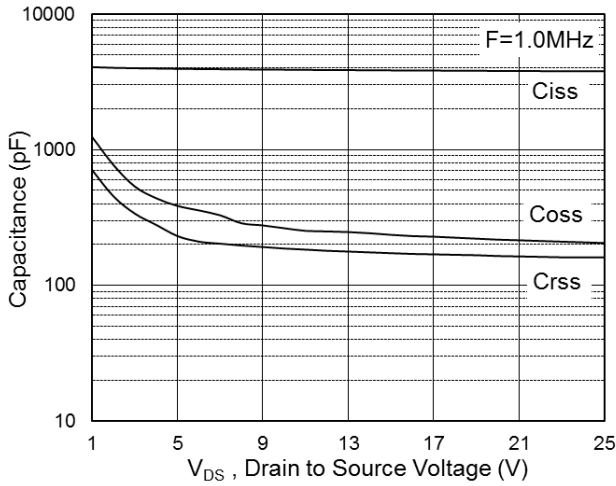
**Fig.4 Gate-Charge Characteristics**



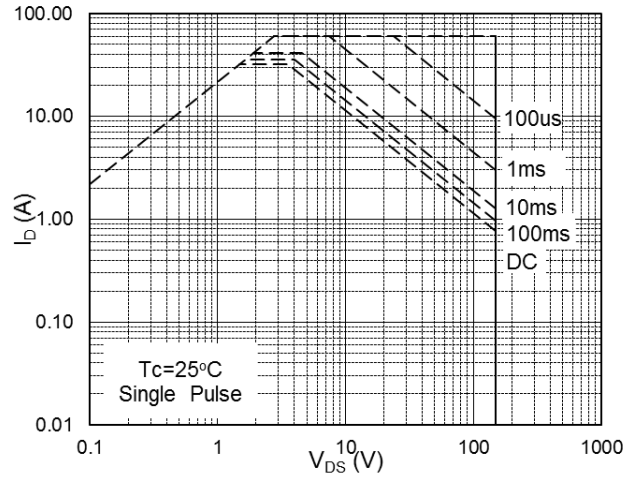
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



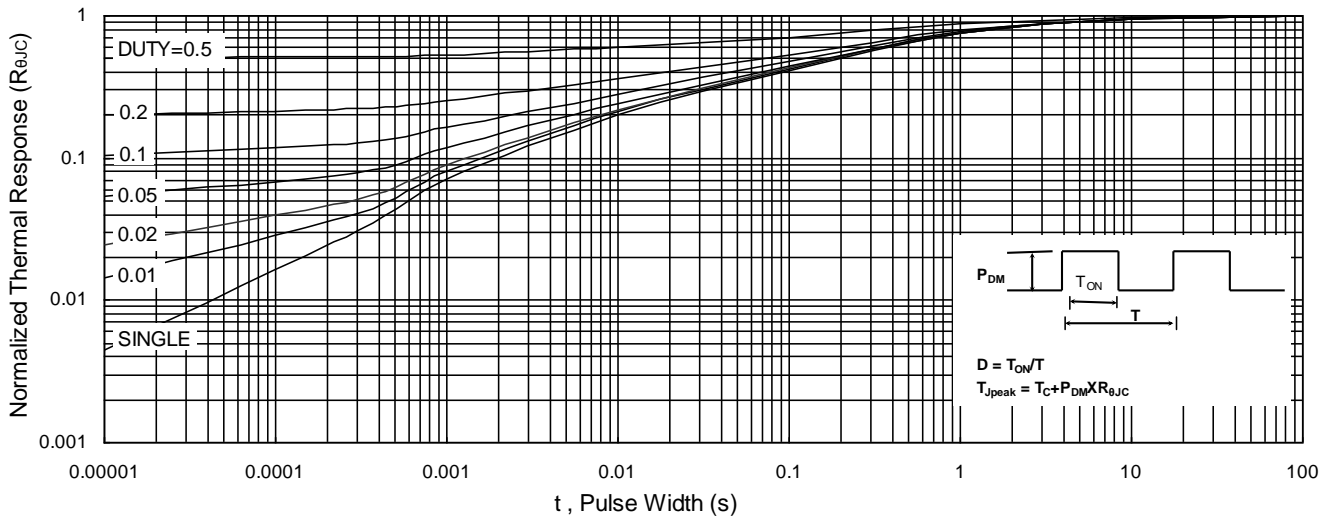
**Fig.6 Normalized  $R_{DSON}$  vs.  $T_J$**



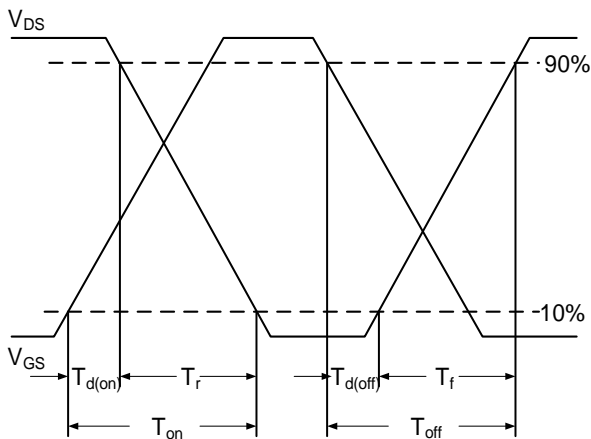
**Fig.7 Capacitance**



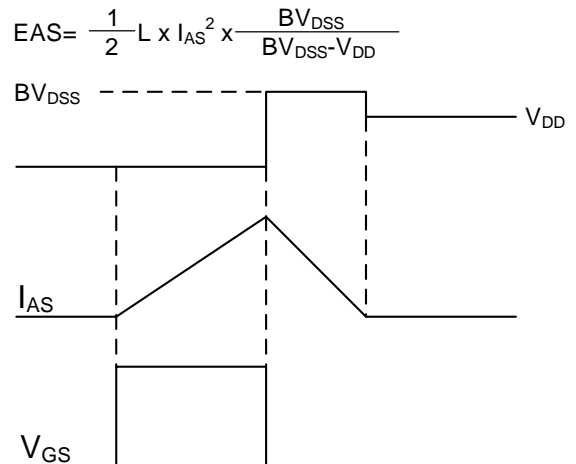
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**

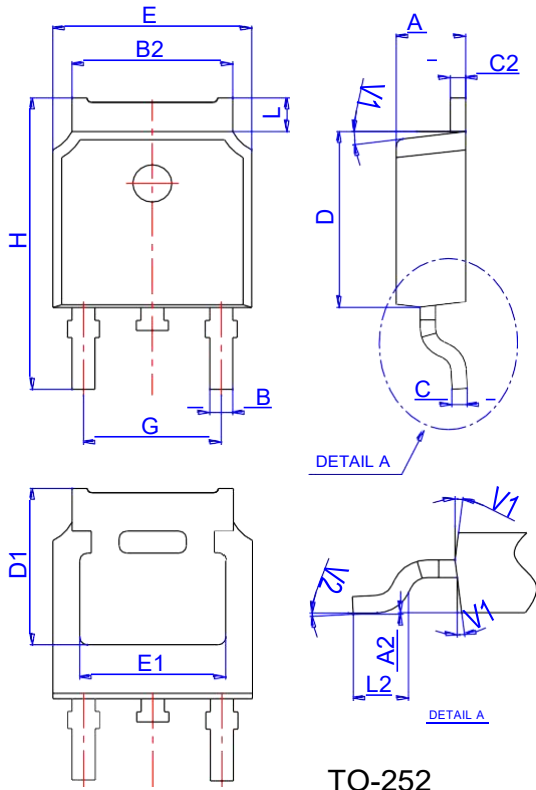


**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Switching Waveform**

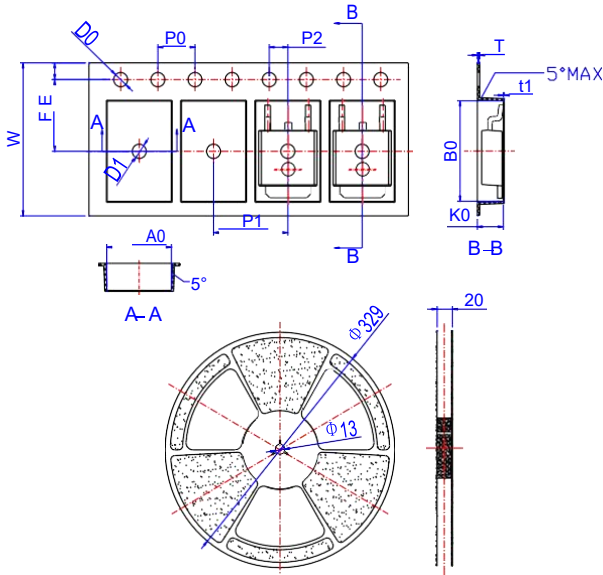
**Package Mechanical Data-TO-252-JQ Single**



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

**Reel Specification-TO-252**



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583